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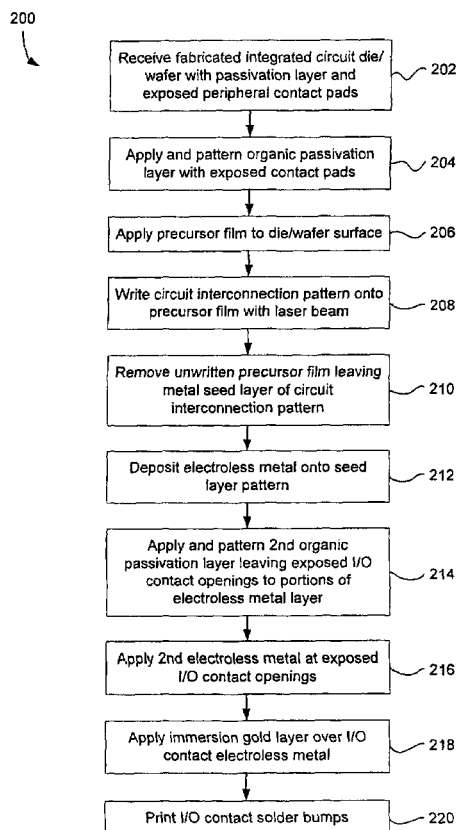
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(54) Title: IMPROVED LASER METALLISATION CIRCUIT FORMATION AND CIRCUITS FORMED THEREBY



(57) Abstract: A laser induced metallisation process for forming circuit interconnections on a substrate involves directing a laser beam to trace over selected portions of the substrate to activate a predetermined circuit interconnection pattern on the surface thereof. A metallic circuit interconnection seed layer is formed on the substrate surface corresponding to the predetermined circuit interconnection pattern, such as by thermal decomposition of metalorganic film or by laser-catalyzing the substrate surface followed by metal electrolyte deposition. The substrate is then subjected to electroless metal plating on the seed layer to form the circuit interconnections. The circuit interconnection formation process can be used to form circuit interconnections on circuit boards or the like, and can also advantageously employed in wafer level chip scale packaging.



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